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1 Electrical ratings

Absolute maximum ratings				
Devemeter		Value		Unit
Parameter	TO-220	TO-247	TO-3PF	Unit
Drain-source voltage (V _{GS} = 0)		1500		V
Gate- source voltage		± 30		V
Drain current (continuous) at T _C = 25 °C	4	4	4 (1)	A
Drain current (continuous) at T _C = 100 °C	2.5	2.5	2.5 ⁽¹⁾	A
Drain current (pulsed)	12	12	12 ⁽¹⁾	А
Total dissipation at $T_{C} = 25 \text{ °C}$	1(60	63	W
Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T _C =25 °C)			3500	V
Storage temperature	-55 to 150			°C
Max. operating junction temperature		150		°C
	ParameterDrain-source voltage ($V_{GS} = 0$)Gate- source voltageDrain current (continuous) at $T_C = 25 \degree C$ Drain current (continuous) at $T_C = 100 \degree C$ Drain current (pulsed)Total dissipation at $T_C = 25 \degree C$ Insulation withstand voltage (RMS)from all three leads to external heatsink (t=1 s; $T_C = 25 \degree C$)Storage temperature	ParameterTO-220Drain-source voltage $(V_{GS} = 0)$ Gate- source voltageDrain current (continuous) at $T_C = 25 \ ^{\circ}C$ Drain current (continuous) at $T_C = 100 \ ^{\circ}C$ Drain current (continuous) at $T_C = 100 \ ^{\circ}C$ Drain current (pulsed)12Total dissipation at $T_C = 25 \ ^{\circ}C$ Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; $T_C = 25 \ ^{\circ}C$)Storage temperature	ValueValueTO-220TO-247Drain-source voltage ($V_{GS} = 0$)1500Gate- source voltage ± 30 Drain current (continuous) at $T_C = 25 \ ^{\circ}C$ 44Drain current (continuous) at $T_C = 100 \ ^{\circ}C$ 2.52.5Drain current (pulsed)1212Total dissipation at $T_C = 25 \ ^{\circ}C$ 160Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; $T_C = 25 \ ^{\circ}C$)-55 to 150	ValueValueTO-247TO-3PFDrain-source voltage ($V_{GS} = 0$)1500Gate- source voltage ± 30 Drain current (continuous) at $T_C = 25 \ ^{\circ}C$ 444 (1)Drain current (continuous) at $T_C = 100 \ ^{\circ}C$ 2.52.52.5 (1)Drain current (pulsed)121212 (1)Total dissipation at $T_C = 25 \ ^{\circ}C$ 16063Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; $T_C = 25 \ ^{\circ}C$)3500Storage temperature-55 to 150

Table 2. Absolute maximum ratings

1. Pulse width limited by safe operating area

Table 3. Thermal data	Table	3.	Thermal	data
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Symbol Parameter			Unit		
Symbol	Symbol Parameter		TO-247	TO-3PF	Onit
R _{thj-case}	Thermal resistance junction-case max	0.78		2	°C/W
R _{thj-amb}	Thermal resistance junction- ambient max	62.5 5		50	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	4	А
E _{AS}	Single pulse avalanche energy (starting $T_j = 25 \text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50 \text{ V}$)	350	mJ



2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	I _D = 1 mA, V _{GS} = 0	1500			V
I _{DSS}	Zero gate voltage Drain current (V _{GS} = 0)	$V_{DS} =$ Max rating $V_{DS} =$ Max rating, $T_{C} =$ 125 °C			10 500	μΑ μΑ
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	3	4	5	V
R _{DS(on}	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2 \text{ A}$		5	7	Ω

Table 5. On/off states

Table 6. Dynamic

	, , , , , , , , , , , , , , , , , , ,	r				
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 2 \text{ A}$	-	3.5		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	1300 120 12		pF pF pF
t _{d(on)} T _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 750 \text{ V}, \text{ I}_{D} = 2 \text{ A},$ $R_{G} = 4.7 \Omega, V_{GS} = 10 \text{ V}$ <i>Figure 19</i>	-	35 30 45 45		ns ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 600 \text{ V}, \text{ I}_{D} = 4 \text{ A},$ $V_{GS} = 10 \text{ V}$ Figure 20	-	30 10 9	50	nC nC nC

1. Pulsed: pulse duration=300 µs, duty cycle 1.5%





Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD} I _{SDM} ⁽¹⁾	Source-drain current Source-drain current (pulsed)		-		4 12	A A
V _{SD} ⁽²⁾	Forward on voltage	$I_{SD} = 4 \text{ A}, V_{GS} = 0$	-		2	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} = 4 A, di/dt = 100 A/μs V _{DD} = 45 V <i>Figure 21</i>	-	510 3 12		ns μC Α
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 4 \text{ A},$ di/dt = 100 A/µs $V_{DD} = 45 \text{ V}, \text{ T}_{j} = 150^{\circ}\text{C}$ Figure 21	-	615 4 12.6		ns μC Α

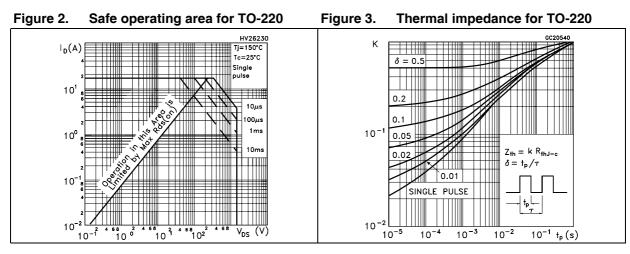
 Table 7.
 Source drain diode

1. Pulse width limited by safe operating area

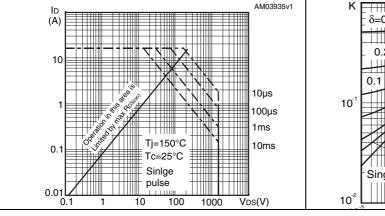
2. Pulsed: pulse duration=300µs, duty cycle 1.5%



2.1 Electrical characteristics (curves)







HV26240

10µ:

100µ 1ms

10m:

 V_{DS} (V)

Figure 6. Safe operating area for TO-247

Tj=150°0

Tc=25*C

Single

puls

 $I_{D}(A)$

10¹

10⁰

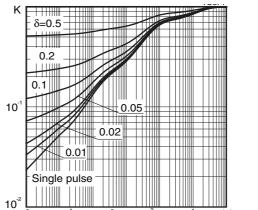
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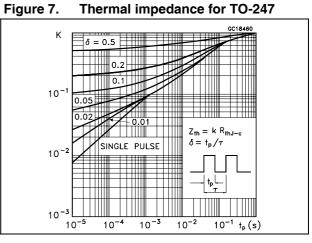
10⁻²

10°

10¹ 10²

Figure 5. Thermal impedance for TO-3PF







HV26055

8 V_{GS}(V)

Transfer characteristics

Vos=30V

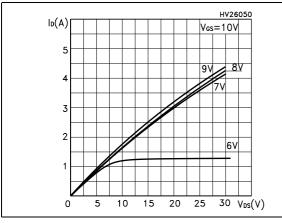
2

4

6

Static drain-source on resistance

Figure 8. Output characteristics





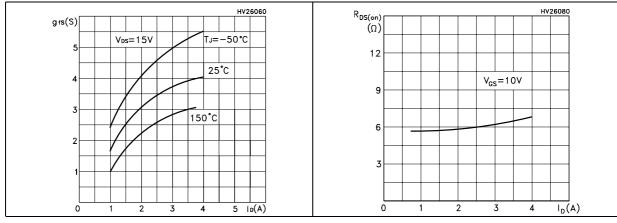


Figure 9.

l₀(A) 5

3

2

0

Figure 11.

Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

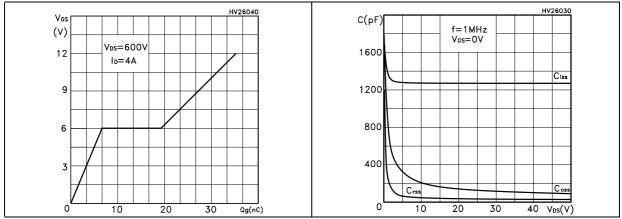




Figure 14. Normalized gate threshold voltage Figure 15. vs temperature

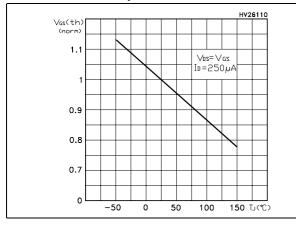


Figure 16. Source-drain diode forward characteristics

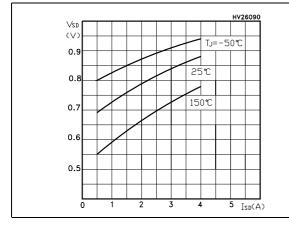
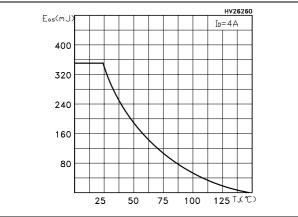


Figure 18. Maximum avalanche energy vs temperature



e 15. Normalized on resistance vs temperature

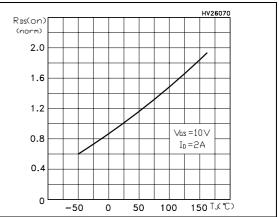
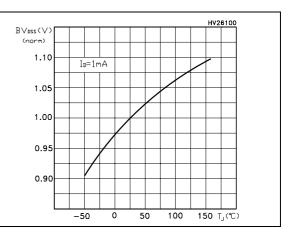


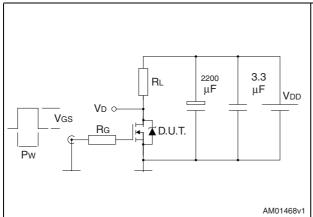
Figure 17. Normalized B_{VDSS} vs temperature





3 Test circuits

Figure 19. Switching times test circuit for resistive load



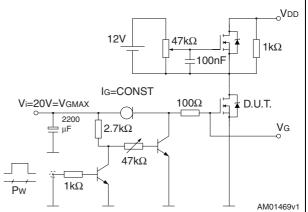
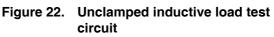
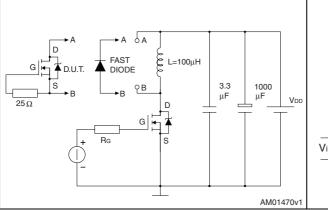
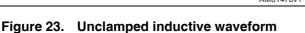


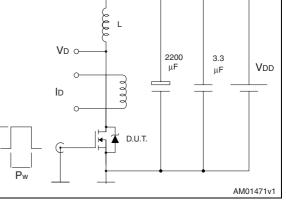
Figure 20. Gate charge test circuit

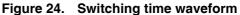
Figure 21. Test circuit for inductive load Figure 21. Switching and diode recovery times

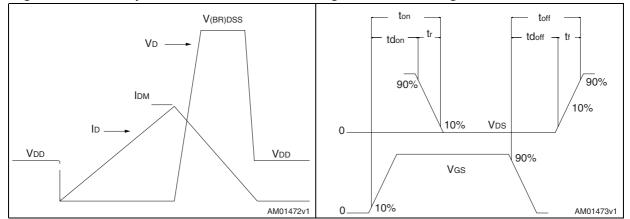














4 Package mechanical data

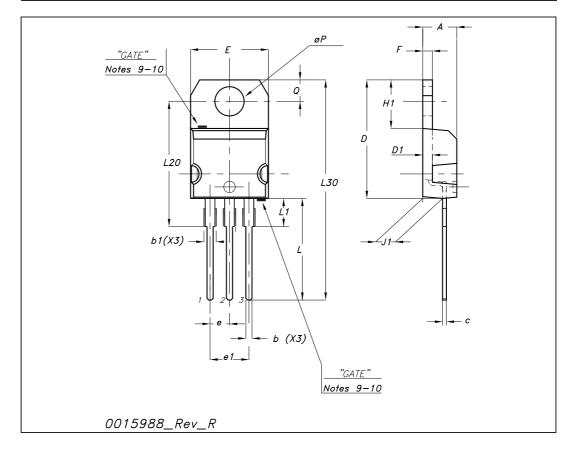
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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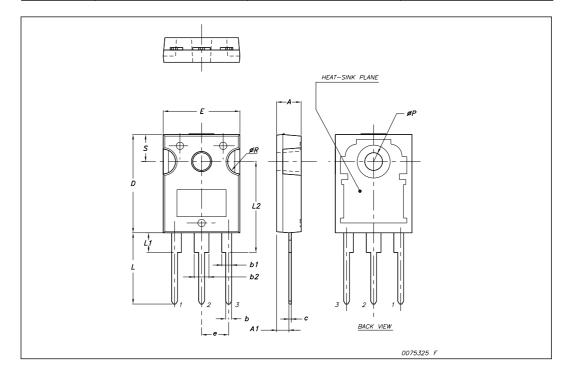
TO-220	mechanical	data

Dim		mm			inch	
Dim	Min	Тур	Max	Min	Тур	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75	1	3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



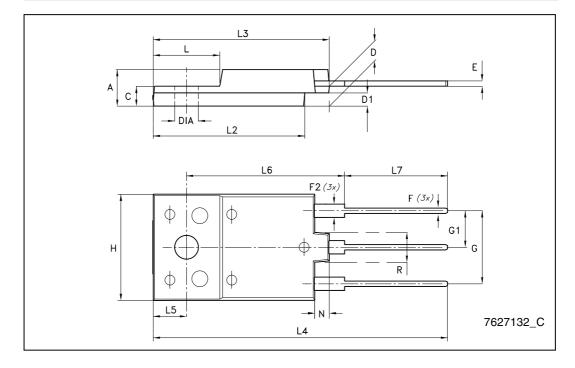


TO-247 Mechanical data				
Dim.		mm.		
	Min.	Тур	Max.	
А	4.85		5.15	
A1	2.20		2.60	
b	1.0		1.40	
b1	2.0		2.40	
b2	3.0		3.40	
С	0.40		0.80	
D	19.85		20.15	
Е	15.45		15.75	
е		5.45		
L	14.20		14.80	
L1	3.70		4.30	
L2		18.50		
øP	3.55		3.65	
øR	4.50		5.50	
S		5.50		





TO-3PF mechanical data					
DIM.					
Divi.	min.	typ	max.		
А	5.30		5.70		
С	2.80		3.20		
D	3.10		3.50		
D1	1.80		2.20		
E	0.80		1.10		
F	0.65		0.95		
F2	1.80		2.20		
G	10.30		11.50		
G1		5.45			
Н	15.30		15.70		
L	9.80	10	10.20		
L2	22.80		23.20		
L3	26.30		26.70		
L4	43.20		44.40		
L5	4.30		4.70		
L6	24.30		24.70		
L7	14.60		15		
Ν	1.80		2.20		
R	3.80		4.20		
Dia	3.40		3.80		





5 Revision history

Date	Revision	Changes
29-Mar-2005	1	Initial release
07-Jul-2005	2	Removed TO-220FP
07-Oct-2005	3	Document status promoted from preliminary data to datasheet
10-Aug-2006	4	Document reformatted, no content change
06-Nov-2007	5	Updated unit on Table 5: On/off states
09-Apr-2008	6	Added new packages: TO-220FH, TO-3PF
21-Jan-2009	7	Remove package TO-220FH
23-Feb-2009	8	Added P _{TOT} value for TO-3PF P _{TOT} (<i>Table 2: Absolute maximum ratings</i>)
23-Jul-2009	9	Added new figures: <i>Figure 4: Safe operating area for TO-3PF</i> and <i>Figure 5: Thermal impedance for TO-3PF</i>



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